



THX15C

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI THX15C** is a Common Emitter Device Designed for High Linearity Class A/AB HF Applications.

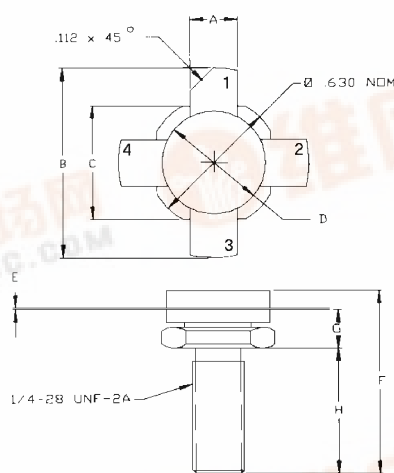
FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	10 A
V_{CB}	110 V
P_{DISS}	233 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JC}	0.75°C/W

PACKAGE STYLE .550 4L STUD



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5.59	.230/5.84
B		1.050/26.67
C	.545/13.84	.555/14.10
D	.495/12.57	.505/12.83
E	.003/0.08	.007/0.18
F		.830/21.08
G	.185/4.70	.198/5.03
H	.497/12.62	.530/13.46

1 = COLLECTOR 2 & 4 = EMITTER
3 = BASE

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 100\text{ mA}$	55			V
BV_{CES}	$I_C = 100\text{ mA}$ $V_{BE} = 0\text{ V}$	110			V
BV_{CBO}	$I_C = 100\text{ mA}$	110			V
BV_{EBO}	$I_E = 10\text{ mA}$	4.0			V
I_{CES}	$V_{CE} = 60\text{ V}$ $V_{BE} = 0\text{ V}$			5.0	mA
I_{CEO}	$V_{CE} = 30\text{ V}$			5.0	mA
h_{FE}	$V_{CE} = 6.0\text{ V}$ $I_C = 1.4\text{ A}$	22.5		27.0	---
C_{ob}	$V_{CB} = 50\text{ V}$ $f = 1.0\text{ MHz}$			220	pF
P_g	$V_{CE} = 50\text{ V}$ $I_{cq} = 100\text{ mA}$	14			dB
IMD_3	$f = 30\text{ MHz}$ $P_{out} = 150\text{ W (PEP)}$	37	-37	-30	dBc
η_c			45		%